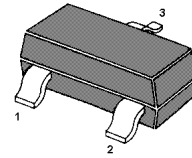


MMBTSC6571

NPN Silicon Epitaxial Planar Transistor

for general amplifier applications.



1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	7	V
Collector Current	I_C	100	mA
Peak Collector Current	I_{CP}	200	mA
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 10\text{ V}$, $I_C = 2\text{ mA}$	h_{FE} Current Gain Group Q R S	160	-	260	-
		210	-	340	-
		290	-	460	-
at $V_{CE} = 2\text{ V}$, $I_C = 100\text{ mA}$		90	-	-	-
Collector Base Cutoff Current at $V_{CB} = 60\text{ V}$	I_{CBO}	-	-	10	nA
Collector Emitter Cutoff Current at $V_{CE} = 50\text{ V}$	I_{CEO}	-	-	100	μA
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	-	10	nA
Collector Base Breakdown Voltage at $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 2\text{ mA}$	$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	7	-	-	V
Collector Emitter Saturation Voltage at $I_C = 100\text{ mA}$, $I_B = 10\text{ mA}$	$V_{CE(sat)}$	-	-	0.3	V
Transistion frequency at $V_{CB} = 10\text{ V}$, $-I_E = 2\text{ mA}$, $f = 200\text{ MHz}$	f_T	-	150	-	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	3.5	-	pF

